

Rec'd PCT/PTO 27 SEP 2004

509,354

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
9 October 2003 (09.10.2003)

PCT

(10) International Publication Number
WO 03/083568 A1

(51) International Patent Classification⁷: **G02F 1/225, 1/017**

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(21) International Application Number: PCT/GB03/01361

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(22) International Filing Date: 27 March 2003 (27.03.2003)

(81) Designated States (*national*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(25) Filing Language: English

(26) Publication Language: English

(84) Designated States (*regional*): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

(30) Priority Data: 0207166.0 27 March 2002 (27.03.2002) GB

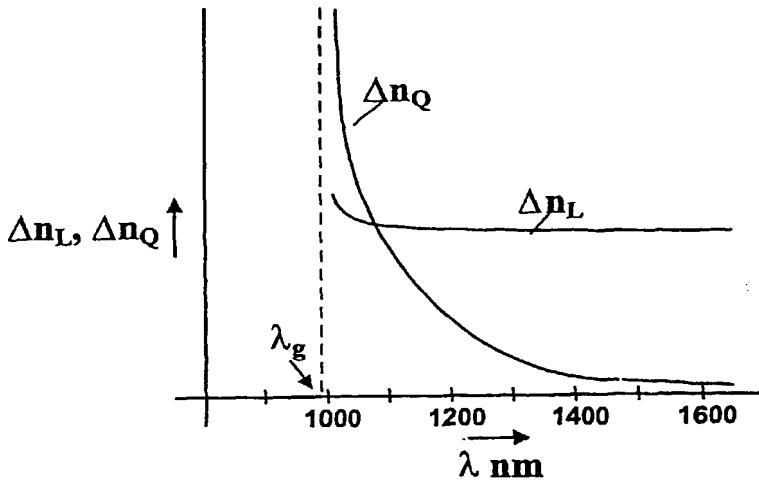
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[Continued on next page]

(54) Title: ELECTRO-OPTIC MODULATORS INCORPORATING QUANTUM DOTS



WO 03/083568 A1

(57) **Abstract:** A modulator is formed of a semiconductor material which utilises the electro-optic effect to achieve a change in the refractive index Δn of the material under the influence of an applied electrical field F (251), in accordance with the equation: $\Delta n = -\frac{1}{2} n_0^3 [rF + sF^2] \equiv \Delta n_L + \Delta n_Q$ where n_0 is the refractive index of the material at zero field, and Δn_L and Δn_Q are the linear and quadratic contributions to the change in refractive index respectively, r is the linear electro-optic coefficient of the material and s is the quadratic electro-optic coefficient of the material incorporating a plurality of quantum dots and operating in a wavelength region where the value of rF is sufficiently greater than the value of sF^2 so as to operate with the dominant effect on the refractive index Δn being contributed by the linear effect. In this way, a device with a wide bandwidth is achieved by appropriately separating the band-gap wavelength (λ_g) and the operating wavelengths (λ).